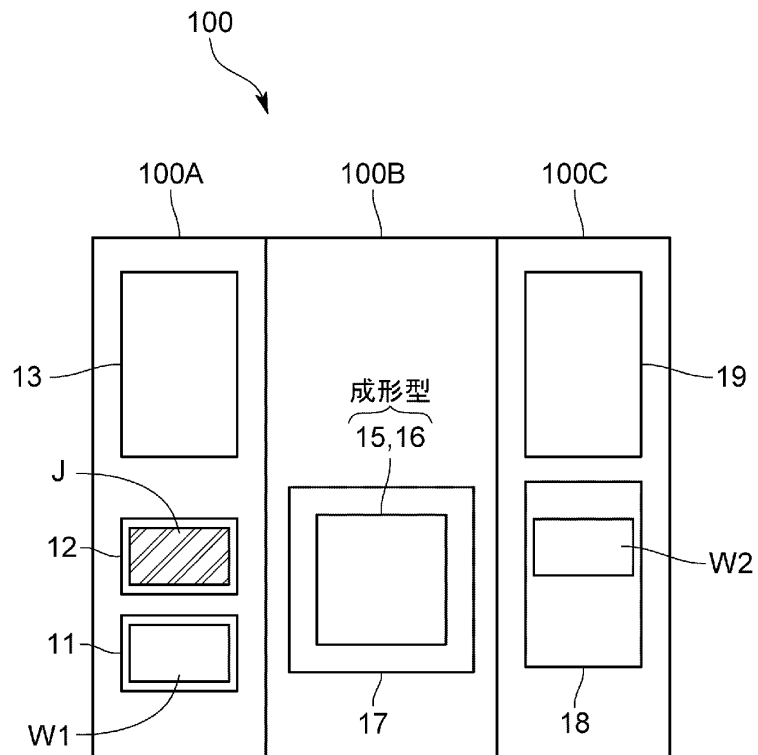
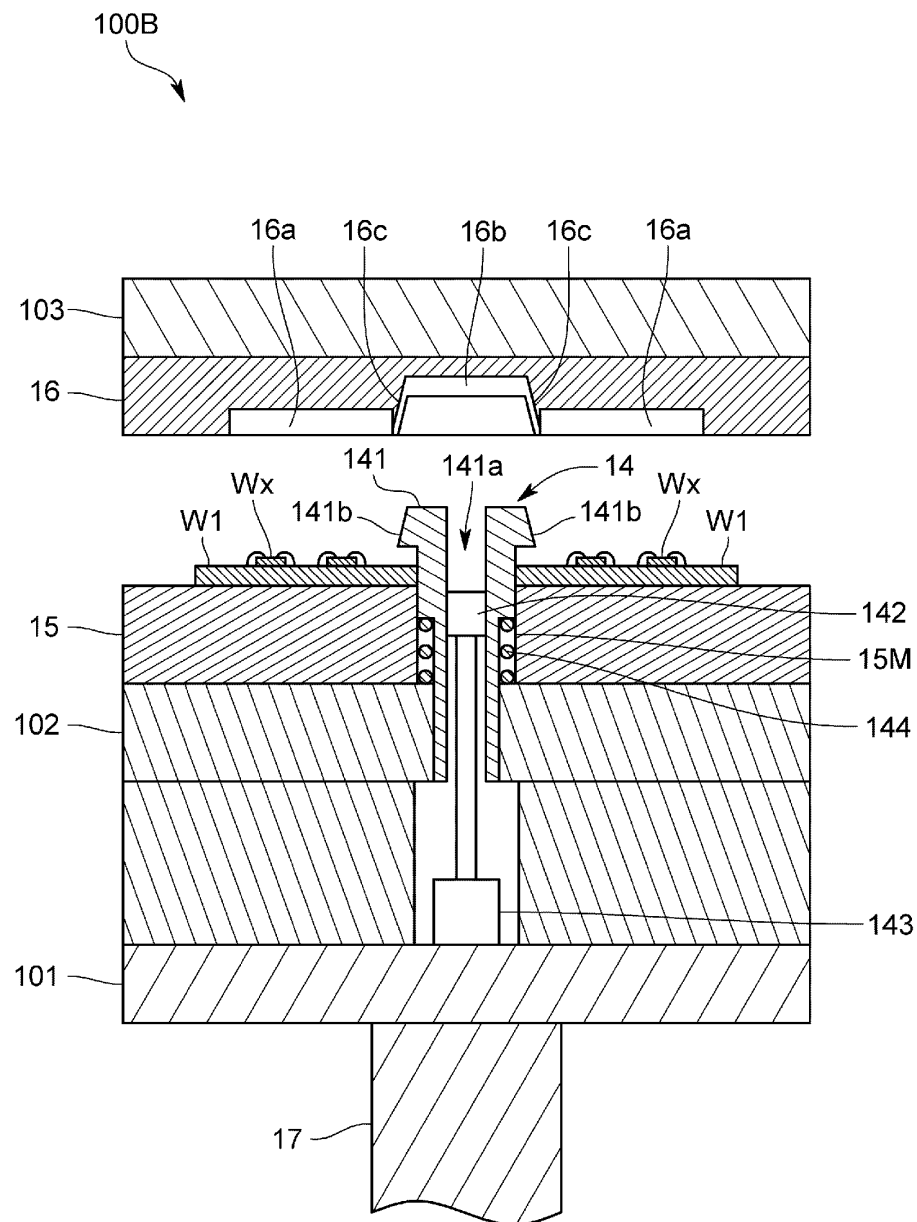


[図1]

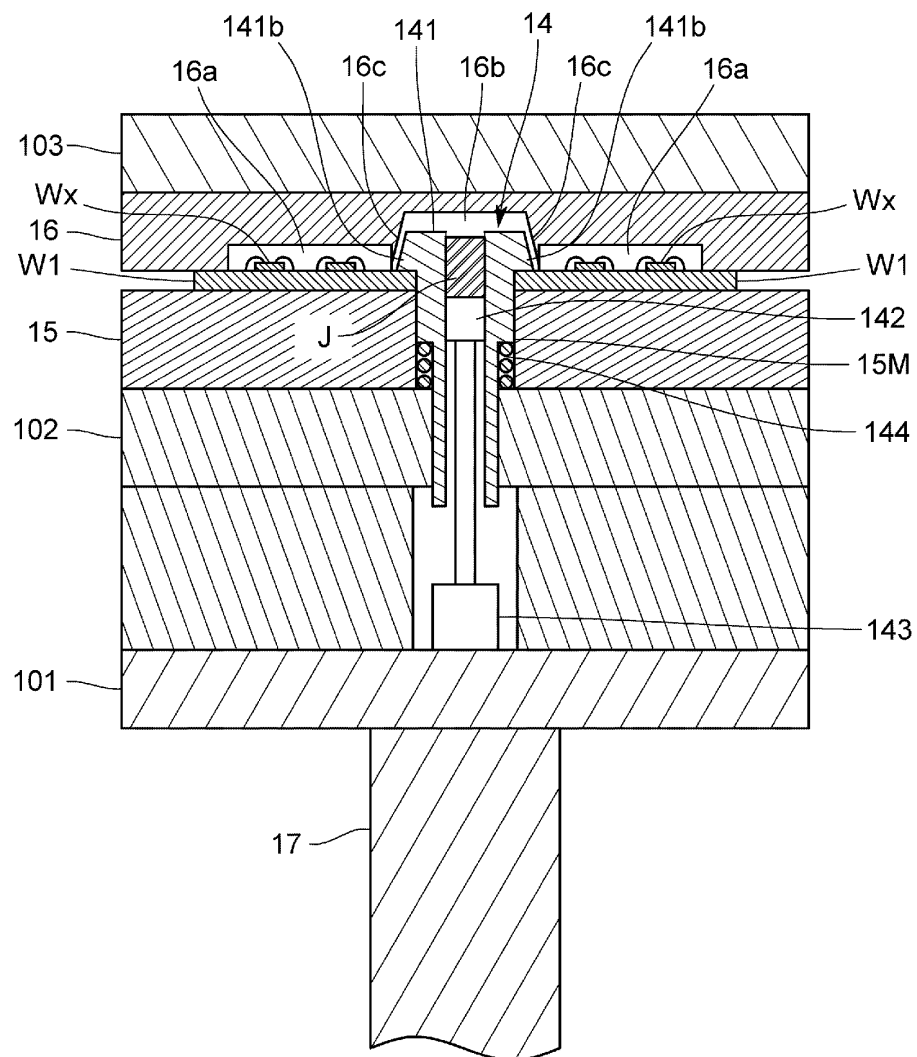


[図2]



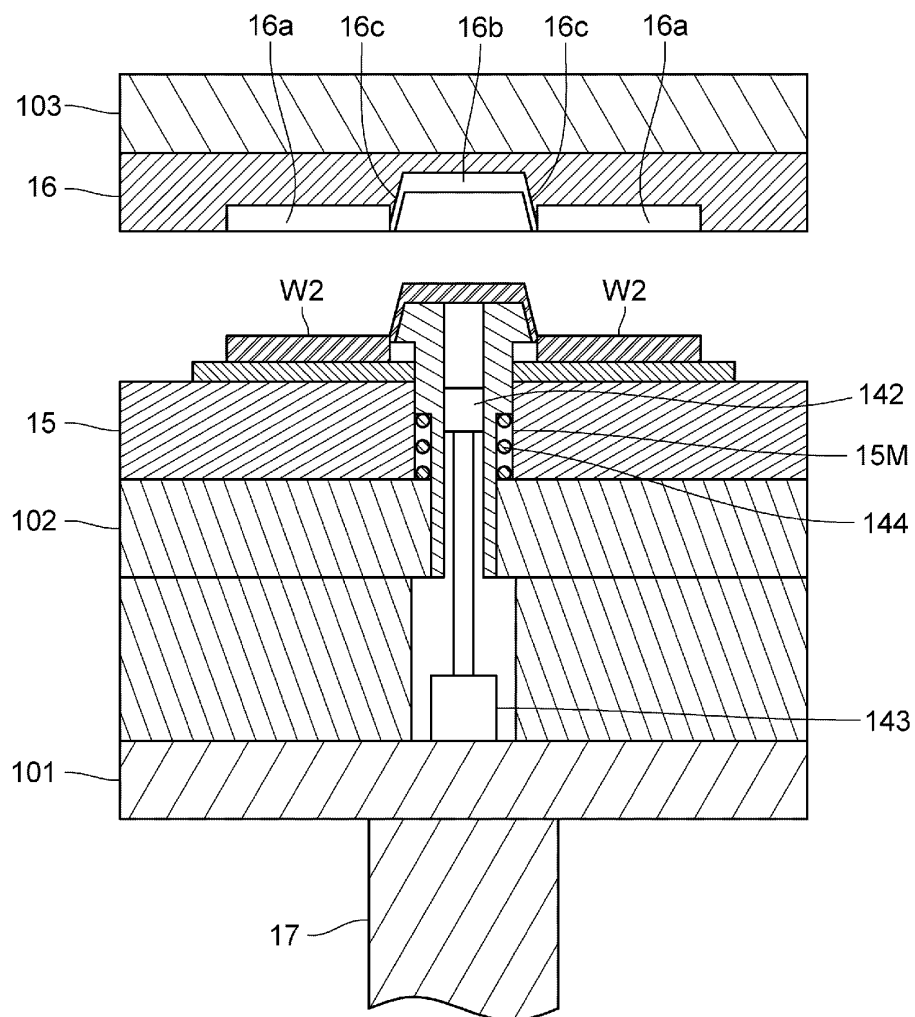


100B



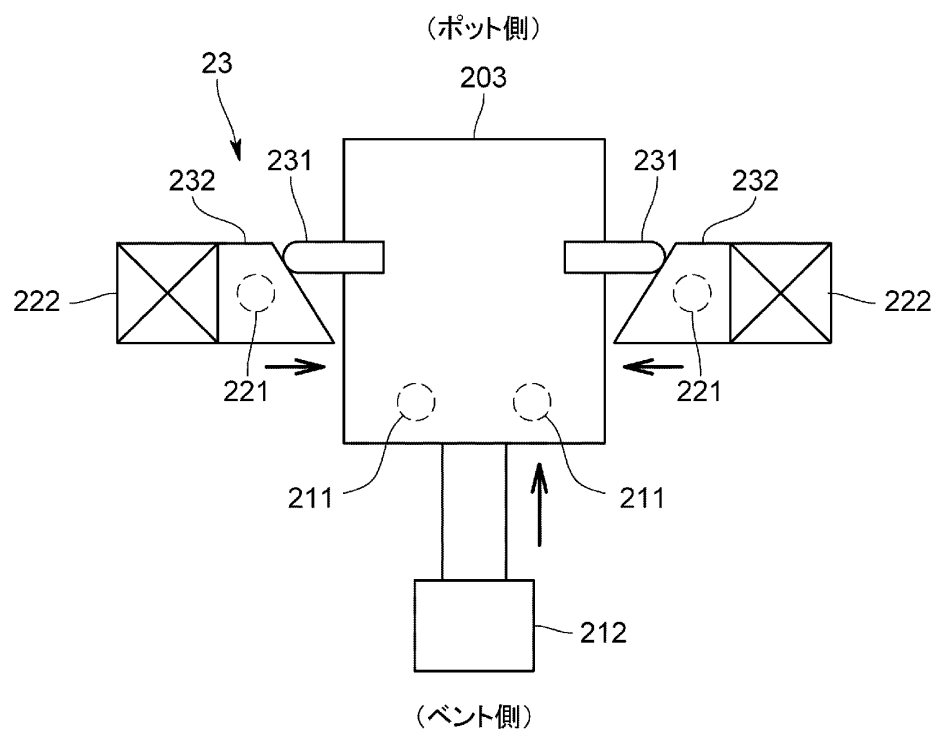
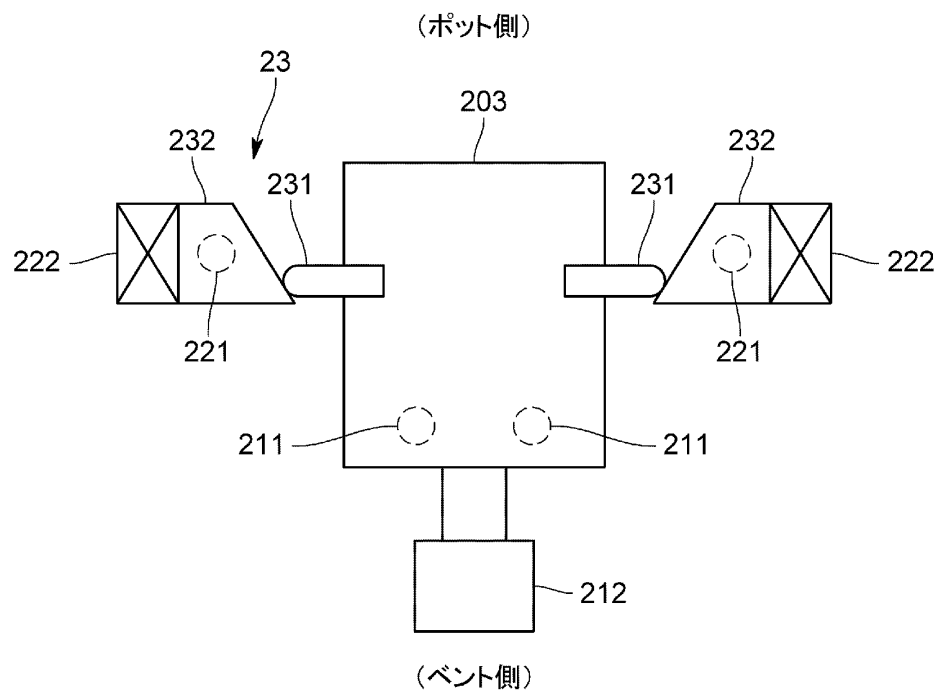
A cross-sectional view of a semiconductor device 100B. The device consists of several stacked layers: a base layer 101, a middle layer 102, and a top layer 103. A central vertical structure 17 passes through all layers. On either side of the center, there are two main regions labeled 141b. Within these regions, there are smaller structures labeled 141 and 14. A junction J is indicated between the top layer 103 and the middle layer 102. Other labels include W1, 16, 15, 15M, 142, 144, and 143, which point to various specific components or interfaces within the device structure.

100B

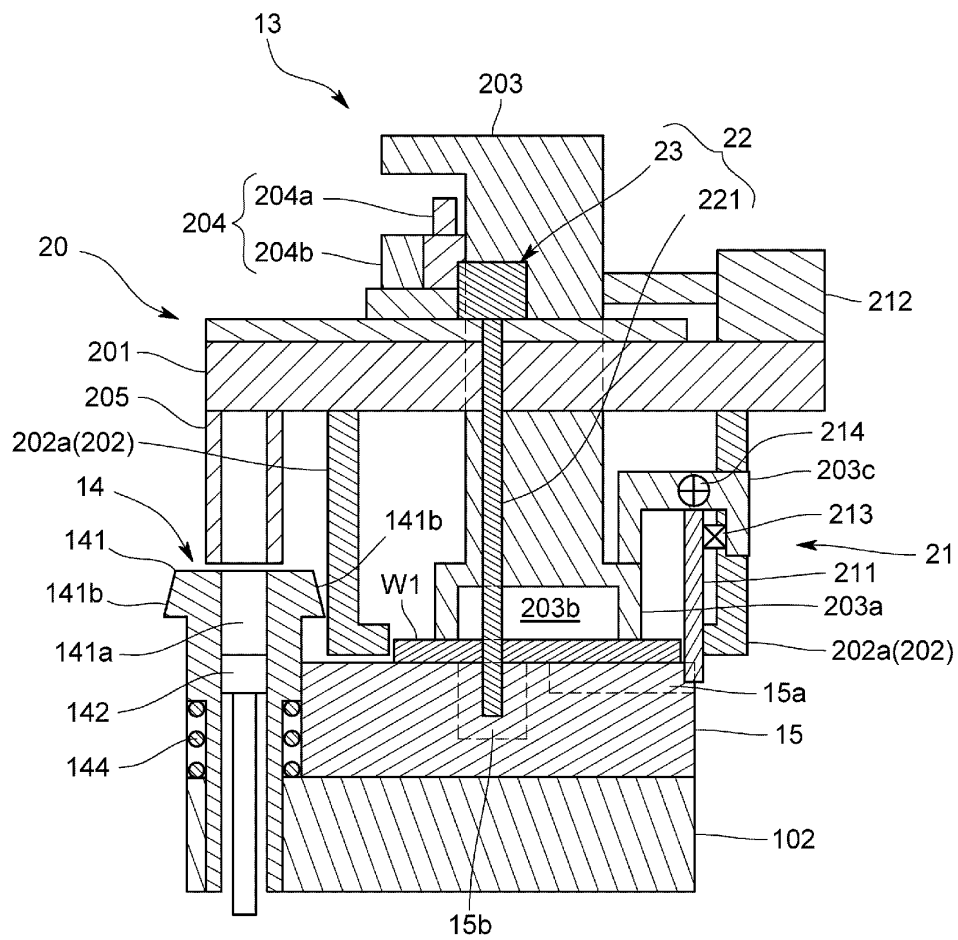




[図8]

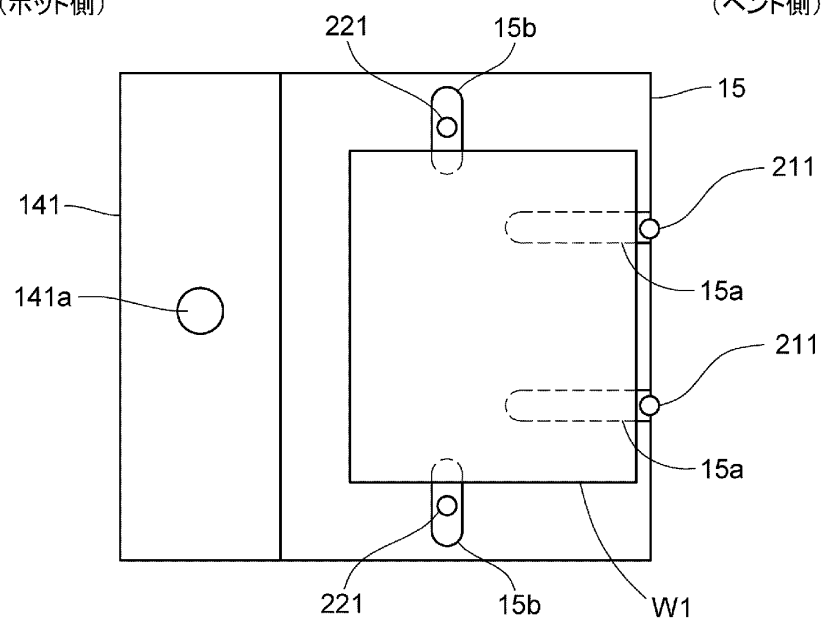


[図9]

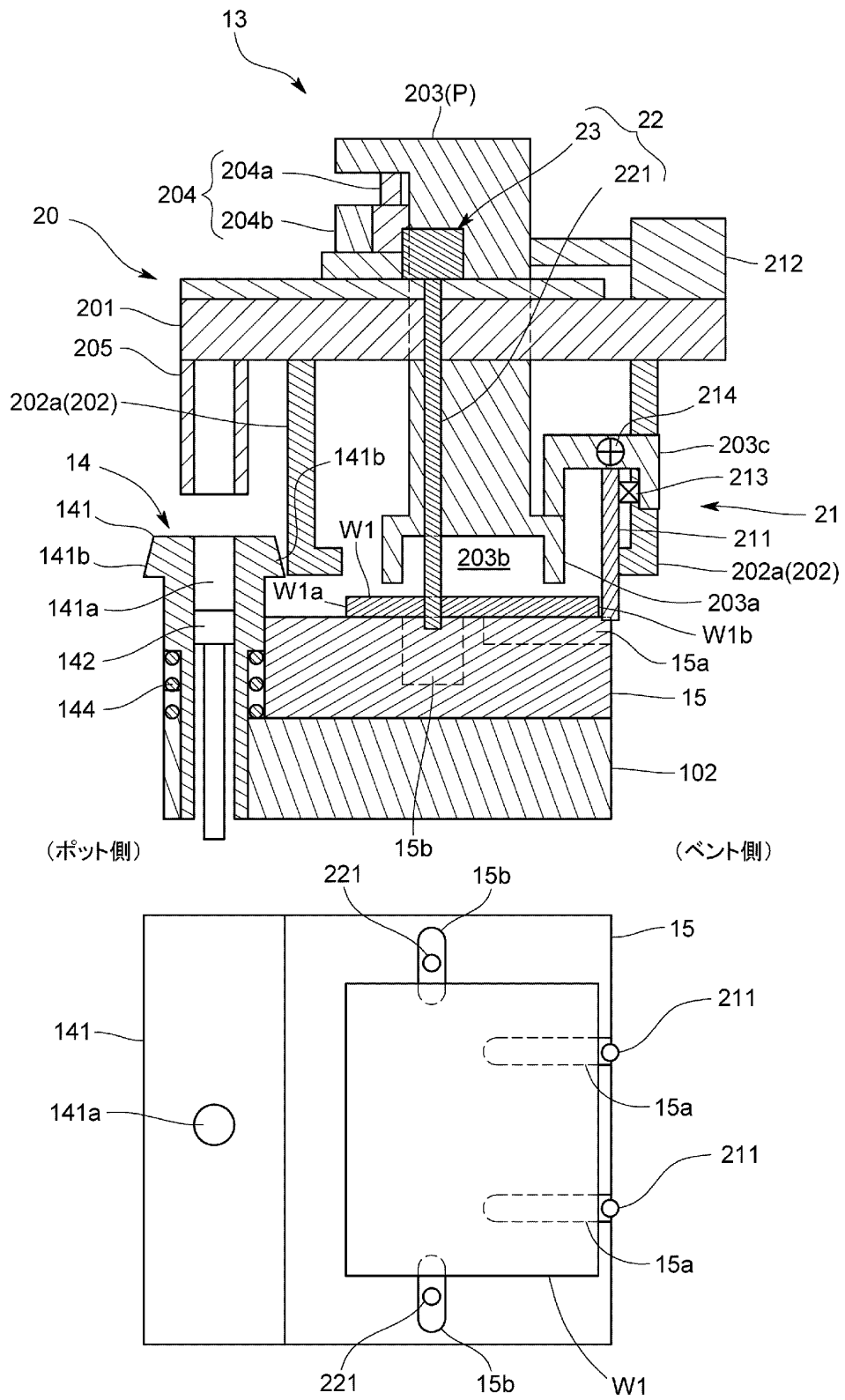


(ポット側)

(ベント側)

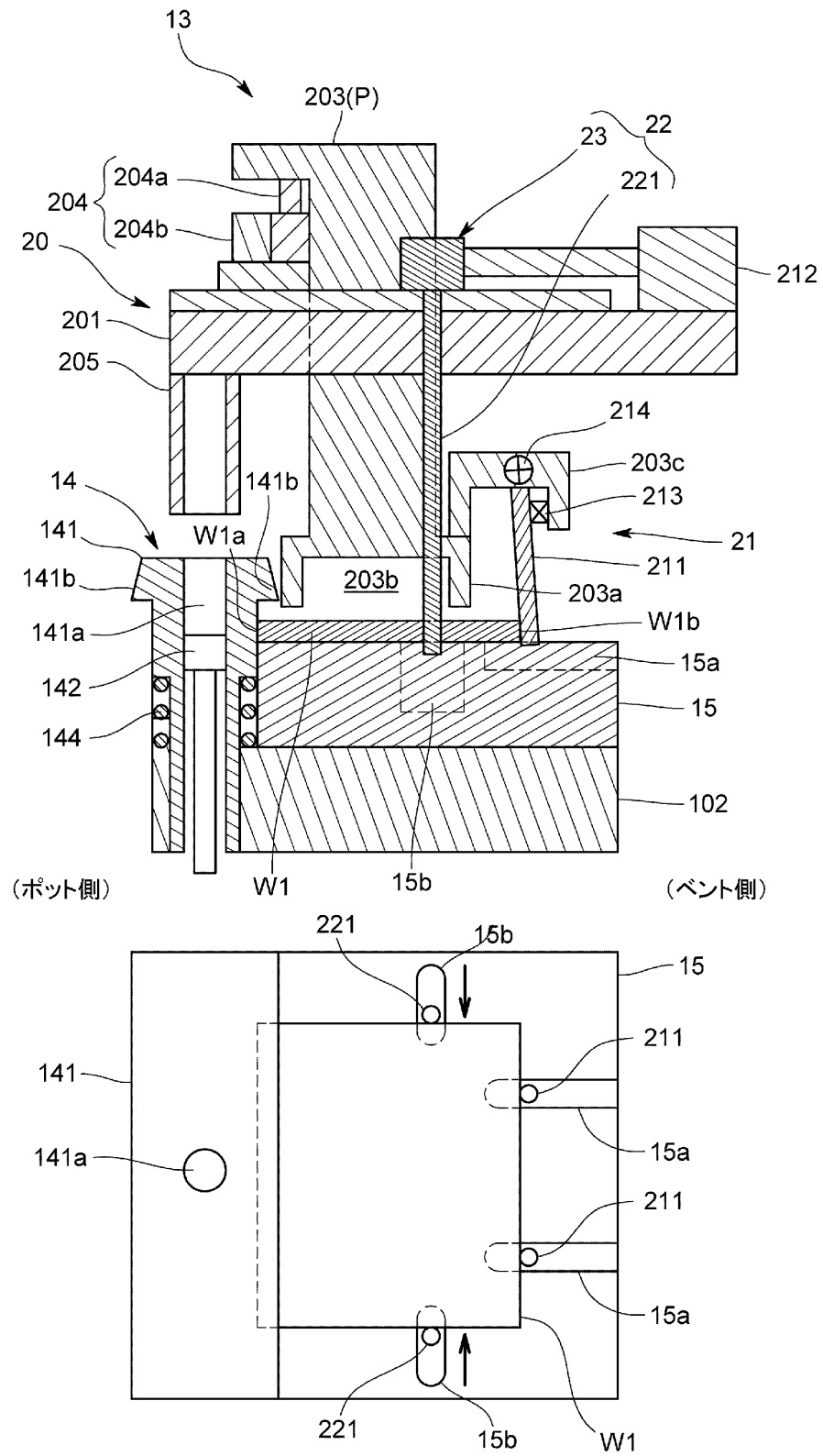


[図10]





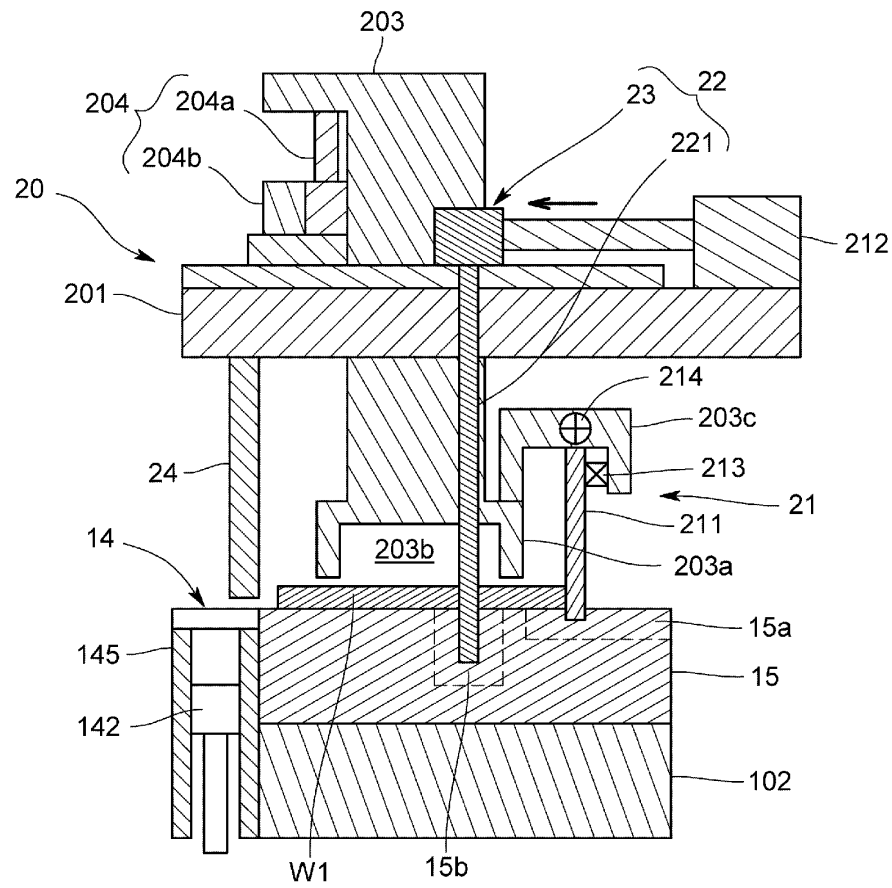
[図12]





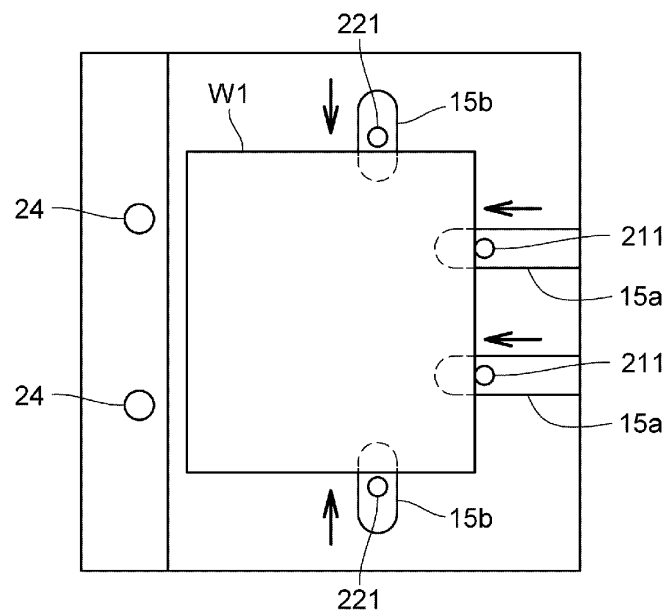


[図15]

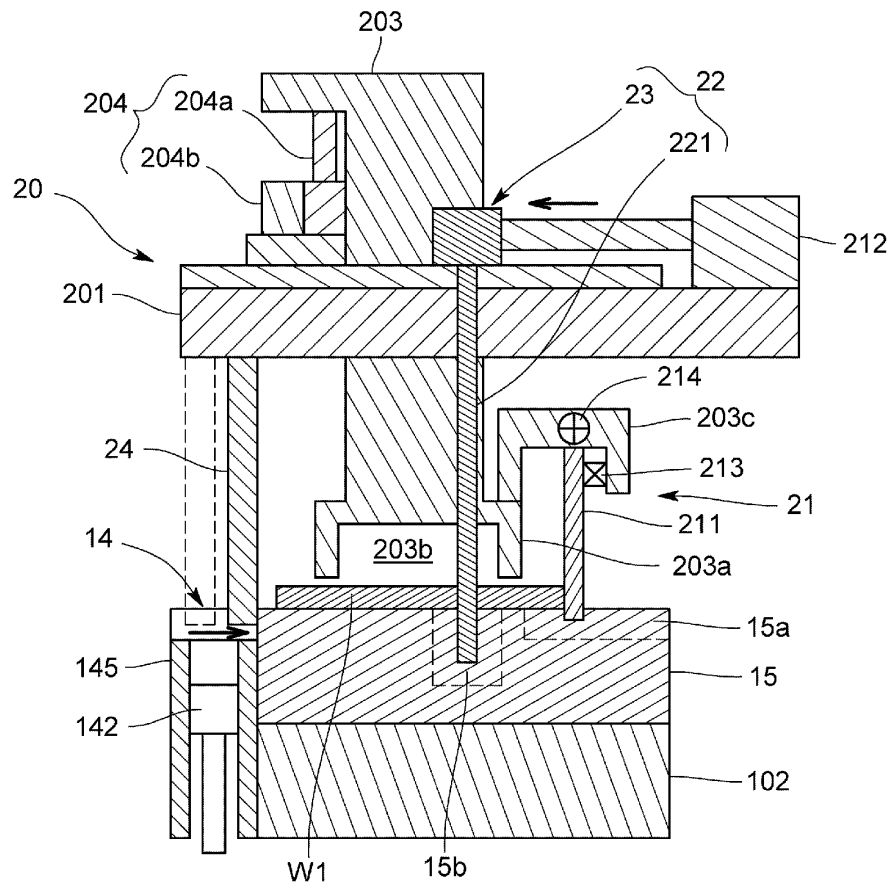


(ポット側)

(ベント側)



[図16]



(ポット側)

(ベント側)

